

# MOSFET

Metal Oxide Semiconductor Field Effect Transistor

## CoolMOS C6

600V CoolMOS™ C6 Power Transistor  
IPx60R520C6

## Data Sheet

Rev. 2.0, 2009-09-17  
Final

Industrial & Multimarket

## 600V CoolMOS™ C6 Power Transistor

IPD60R520C6, IPP60R520C6  
IPA60R520C6

### 1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ C6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The offered devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter, and cooler.

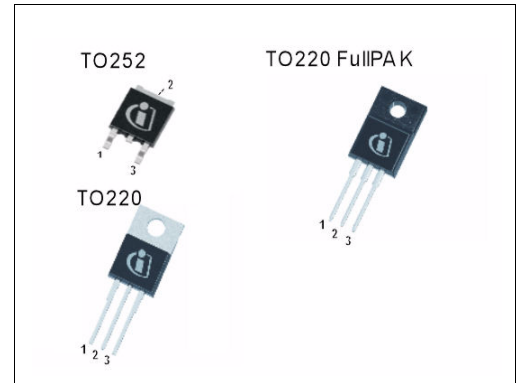
#### Features

- Extremely low losses due to very low FOM  $R_{DS(on)} \cdot Q_g$  and  $E_{oss}$
- Very high commutation ruggedness
- Easy to use/drive
- JEDEC<sup>1)</sup> qualified, Pb-free plating

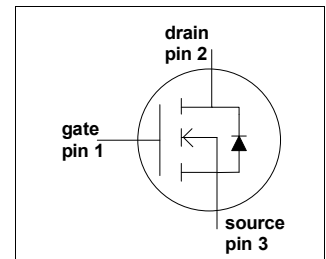
#### Applications

PFC stages, hard switching PWM stages and resonant switching PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom, UPS and Solar.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.



RoHS



**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	0.52	$\Omega$
$Q_{g,typ}$	23.4	nC
$I_{D,pulse}$	22	A
$E_{oss} @ 400V$	2.1	$\mu J$
Body diode $di/dt$	500	A/ $\mu s$

Type / Ordering Code	Package	Marking	Related Links
IPD60R520C6	PG-TO252	6R520C6	<a href="#">IFX C6 Product Brief</a> <a href="#">IFX C6 Portfolio</a> <a href="#">IFX CoolMOS Webpage</a> <a href="#">IFX Design tools</a>
IPP60R520C6	PG-TO220		
IPA60R520C6	PG-TO220 FullPAK		

1) J-STD20 and JESD22

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## 2 Maximum ratings

at  $T_j = 25\text{ °C}$ , unless otherwise specified.

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$	-	-	8.1	A	$T_C = 25\text{ °C}$
				5.1		$T_C = 100\text{ °C}$
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	-	-	22	A	$T_C = 25\text{ °C}$
Avalanche energy, single pulse	$E_{AS}$	-	-	153	mJ	$I_D = 1.4\text{ A}, V_{DD} = 50\text{ V}$ (see table 21)
Avalanche energy, repetitive	$E_{AR}$	-	-	0.23		$I_D = 1.3\text{ A}, V_{DD} = 50\text{ V}$
Avalanche current, repetitive	$I_{AR}$	-	-	1.4	A	
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	$V_{DS} = 0 \dots 480\text{ V}$
Gate source voltage	$V_{GS}$	-20	-	20	V	static
		-30		30		AC ( $f > 1\text{ Hz}$ )
Power dissipation for TO-220, TO-252	$P_{tot}$	-	-	66	W	$T_C = 25\text{ °C}$
Power dissipation for TO-220 FullPAK	$P_{tot}$	-	-	29	W	$T_C = 25\text{ °C}$
Operating and storage temperature	$T_j, T_{stg}$	-55	-	150	°C	
Mounting torque TO-220		-	-	60	Ncm	M3 and M3.5 screws
Mounting torque TO-220 FullPAK				50		M2.5 screws
Continuous diode forward current	$I_S$	-	-	7	A	$T_C = 25\text{ °C}$
Diode pulse current <sup>2)</sup>	$I_{S,pulse}$	-	-	22	A	$T_C = 25\text{ °C}$
Reverse diode dv/dt <sup>3)</sup>	dv/dt	-	-	15	V/ns	$V_{DS} = 0 \dots 400\text{ V}, I_{SD} \leq I_D,$ $T_j = 25\text{ °C}$
Maximum diode commutation speed <sup>3)</sup>	di/dt			500	A/μs	(see table 22)

1) Limited by  $T_{j,max}$ . Maximum duty cycle  $D = 0.75$

2) Pulse width  $t_p$  limited by  $T_{j,max}$

3) Identical low side and high side switch with identical  $R_G$

### 3 Thermal characteristics

**Table 3 Thermal characteristics TO-220 (IP60R520C6)**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.9	°C/W	leaded
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	62		
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

**Table 4 Thermal characteristics TO-220FullIPAK (IPA60R520C6)**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	4.3	°C/W	leaded
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	80		
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

**Table 5 Thermal characteristics TO-252 (IPD60R520C6)**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.9	°C/W	SMD version, device on PCB, minimal footprint
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	62		
				35		
Soldering temperature, wave- & reflow soldering allowed	$T_{sold}$	-	-	260	°C	reflow MSL1

1) Device on 40mm\*40mm\*1.5mm one layer epoxy PCB FR4 with 6cm<sup>2</sup> copper area (thickness 70µm) for drain connection. PCB is vertical without air stream cooling.

## 4 Electrical characteristics

Electrical characteristics, at  $T_J=25\text{ °C}$ , unless otherwise specified.

**Table 6 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS}=0\text{ V}$ , $I_D=0.25\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.5	3	3.5		$V_{DS}=V_{GS}$ , $I_D=0.23\text{ mA}$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	$\mu\text{A}$	$V_{DS}=600\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_J=25\text{ °C}$
		-	10	-		$V_{DS}=600\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_J=150\text{ °C}$
Gate-source leakage current	$I_{GSS}$	-	-	100	nA	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.47	0.52	$\Omega$	$V_{GS}=10\text{ V}$ , $I_D=2.8\text{ A}$ , $T_J=25\text{ °C}$
		-	1.22	-		$V_{GS}=10\text{ V}$ , $I_D=2.8\text{ A}$ , $T_J=150\text{ °C}$
Gate resistance	$R_G$	-	17.5	-	$\Omega$	$f=1\text{ MHz}$ , open drain

**Table 7 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition	
		Min.	Typ.	Max.			
Input capacitance	$C_{iss}$	-	512	-	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=100\text{ V}$ , $f=1\text{ MHz}$	
Output capacitance	$C_{oss}$	-	35	-			
Effective output capacitance, energy related <sup>1)</sup>	$C_{o(er)}$	-	23	-			$V_{GS}=0\text{ V}$ , $V_{DS}=0\dots480\text{ V}$
Effective output capacitance, time related <sup>2)</sup>	$C_{o(tr)}$	-	100	-			$I_D=\text{constant}$ , $V_{GS}=0\text{ V}$ $V_{DS}=0\dots480\text{ V}$
Turn-on delay time	$t_{d(on)}$	-	13	-	ns	$V_{DD}=400\text{ V}$ , $V_{GS}=13\text{ V}$ , $I_D=3.5\text{ A}$ , $R_G=6.8\text{ }\Omega$ (see table 20)	
Rise time	$t_r$	-	10	-			
Turn-off delay time	$t_{d(off)}$	-	85	-			
Fall time	$t_f$	-	14	-			

1)  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$

2)  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$

**Table 8 Gate charge characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$	-	2.8	-	nC	$V_{DD}=480\text{ V}$ , $I_D=3.5\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	$Q_{gd}$	-	12	-		
Gate charge total	$Q_g$	-	23.4	-		
Gate plateau voltage	$V_{\text{plateau}}$	-	5.4	-	V	

**Table 9 Reverse diode characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	$V_{SD}$	-	0.9	-	V	$V_{GS}=0\text{ V}$ , $I_F=3.5\text{ A}$ , $T_j=25\text{ °C}$
Reverse recovery time	$t_{rr}$	-	260	-	ns	$V_R=400\text{ V}$ , $I_F=3.5\text{ A}$ ,
Reverse recovery charge	$Q_{rr}$	-	2.5	-	$\mu\text{C}$	$di_F/dt=100\text{ A}/\mu\text{s}$ (see table 22)
Peak reverse recovery current	$I_{rrm}$	-	18	-	A	

5 Electrical characteristics diagrams

Table 10

Power dissipation TO-220, TO-252	Power dissipation TO-220 FullPAK
$P_{tot} = f(T_C)$	$P_{tot} = f(T_C)$

Table 11

Max. transient thermal impedance TO-220, TO-252	Max. transient thermal impedance TO-220 FullPAK
$Z_{(thJC)} = f(t_p)$ ; parameter: $D = t_p / T$	$Z_{(thJC)} = f(t_p)$ ; parameter: $D = t_p / T$



Electrical characteristics diagrams

Table 12

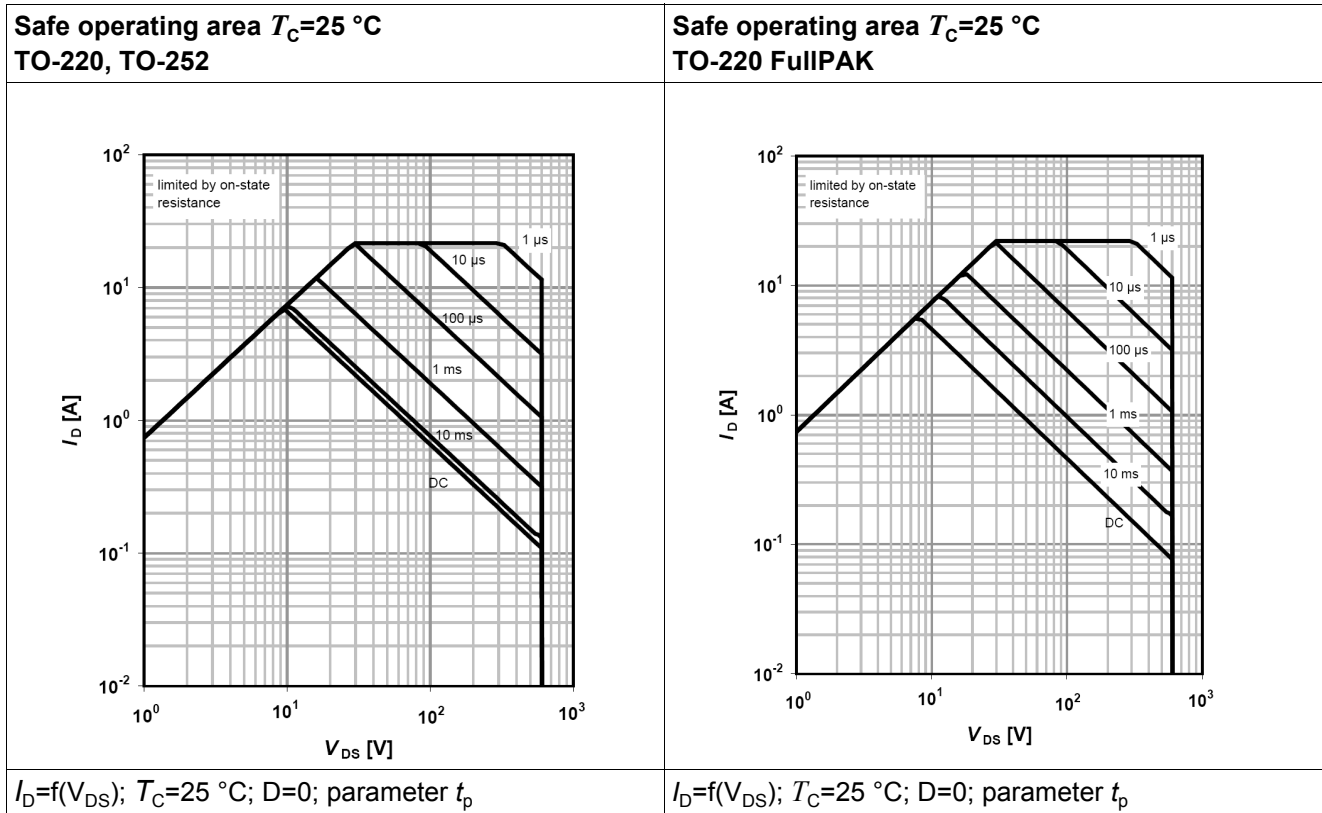


Table 13

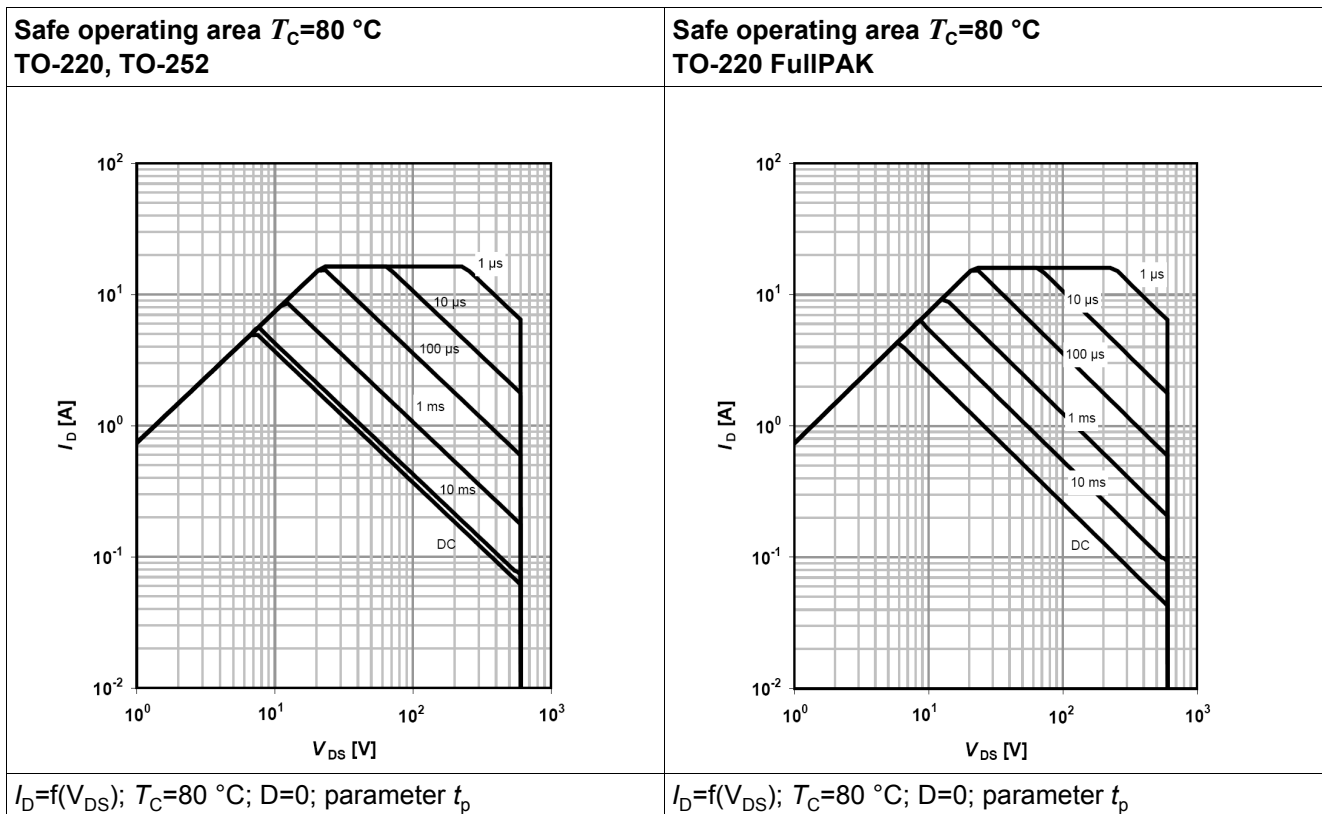


Table 14

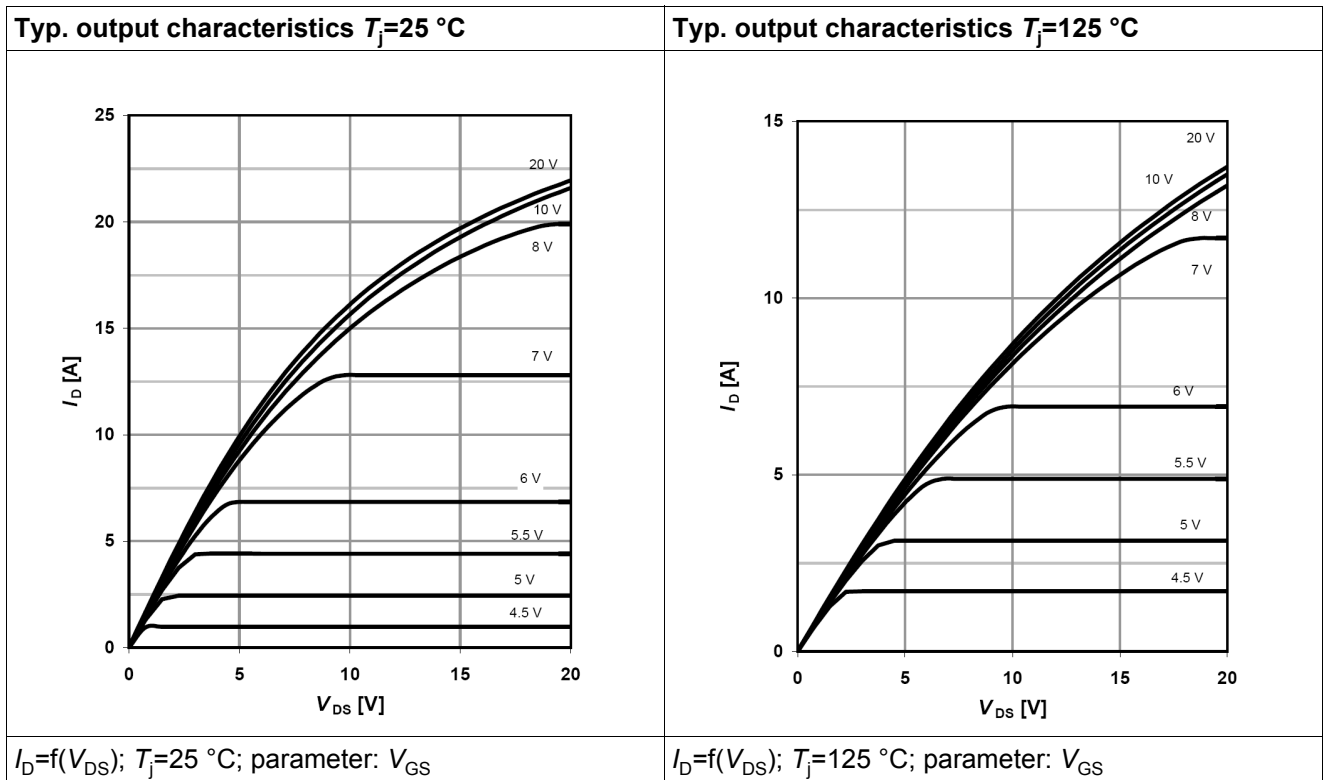


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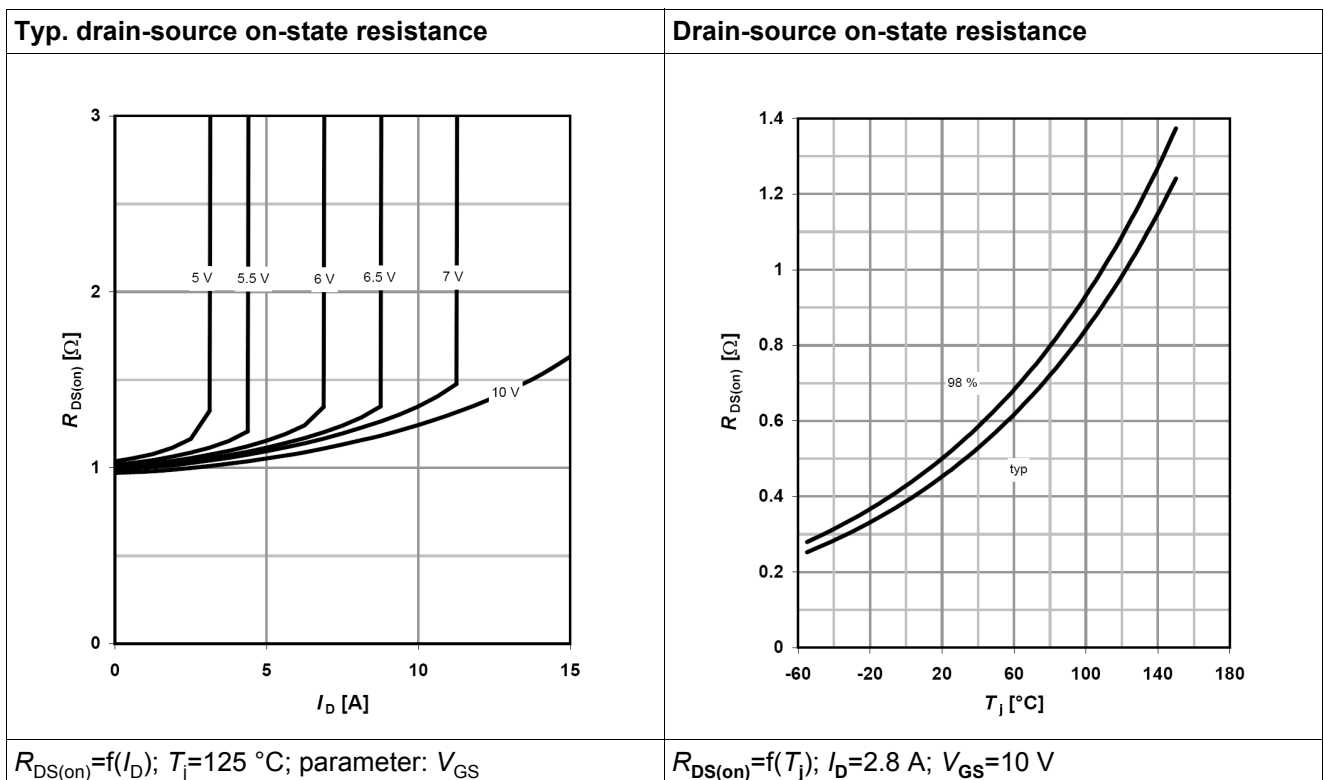


Table 16

Typ. transfer characteristics	Typ. gate charge
$I_D = f(V_{GS}); V_{DS} = 20V$	$V_{GS} = f(Q_{gate}); I_D = 3.5 A \text{ pulsed}$

Table 17

Avalanche energy	Drain-source breakdown voltage
$E_{AS} = f(T_j); I_D = 1.4 A; V_{DD} = 50 V$	$V_{BR(DSS)} = f(T_j); I_D = 0.25 mA$

Table 18

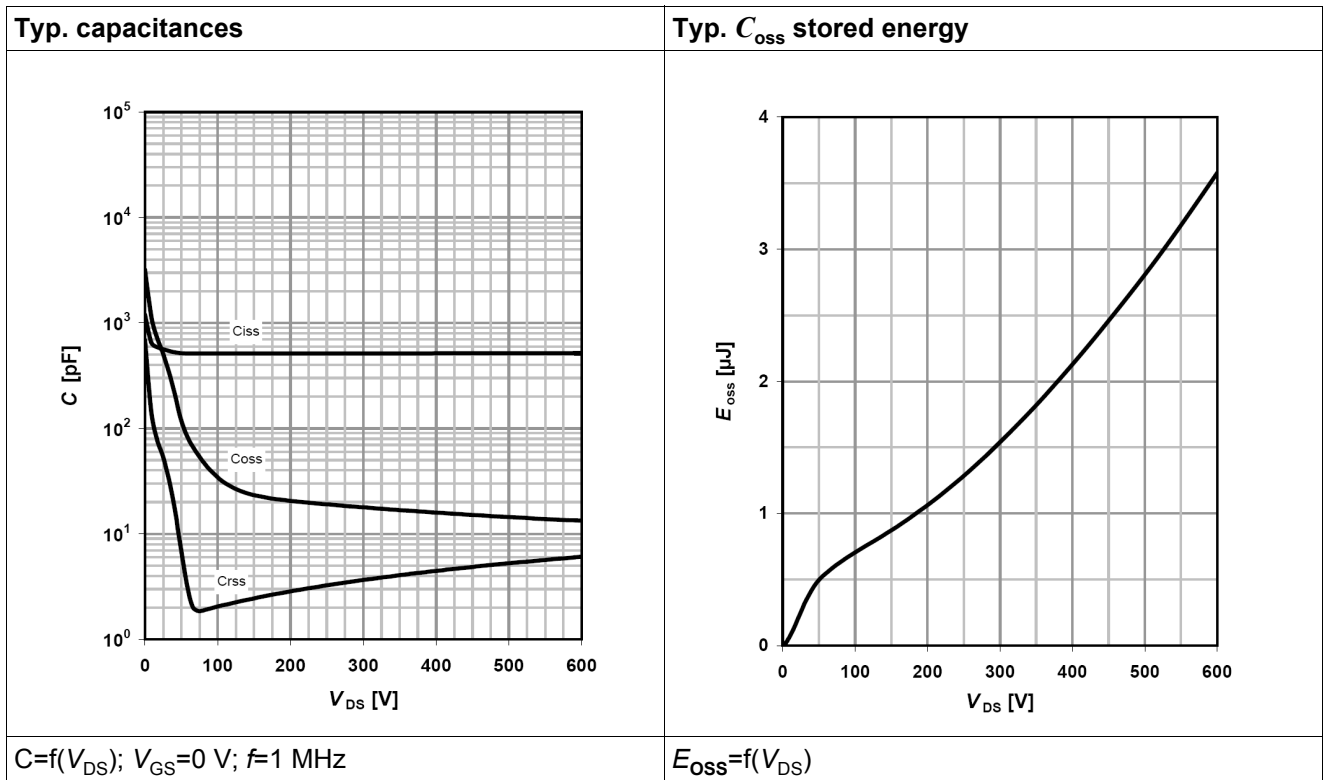
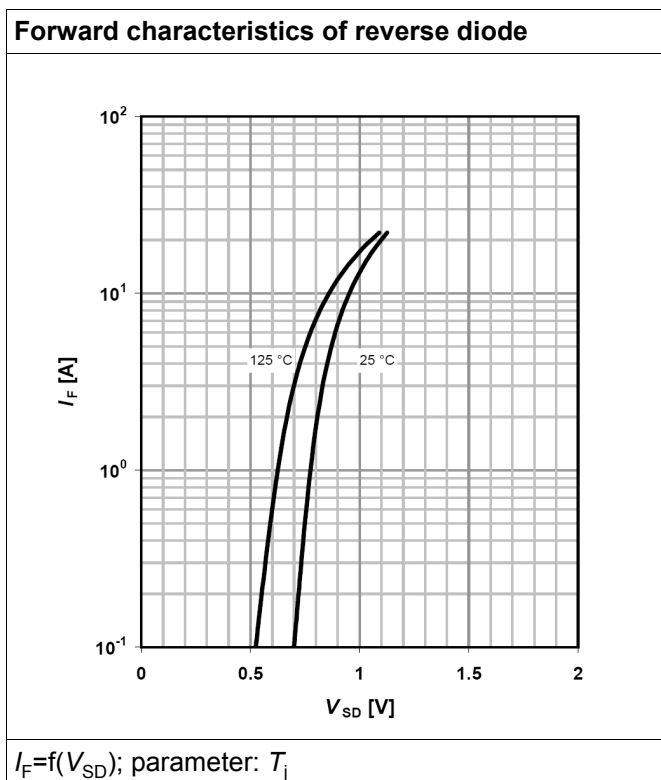


Table 19



## 6 Test circuits

Table 20 Switching times test circuit and waveform for inductive load

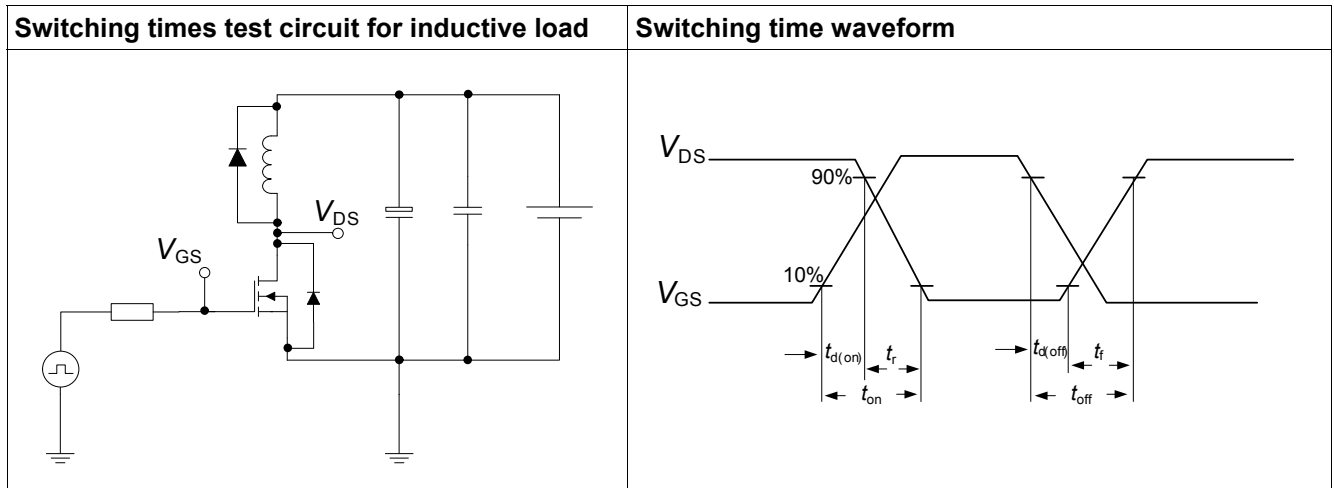


Table 21 Unclamped inductive load test circuit and waveform

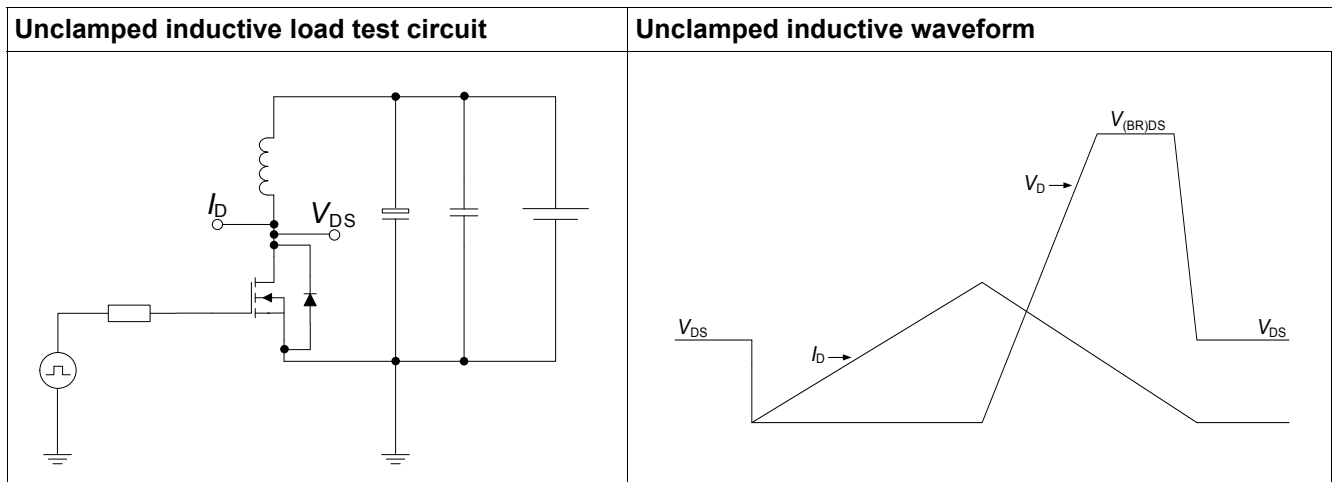
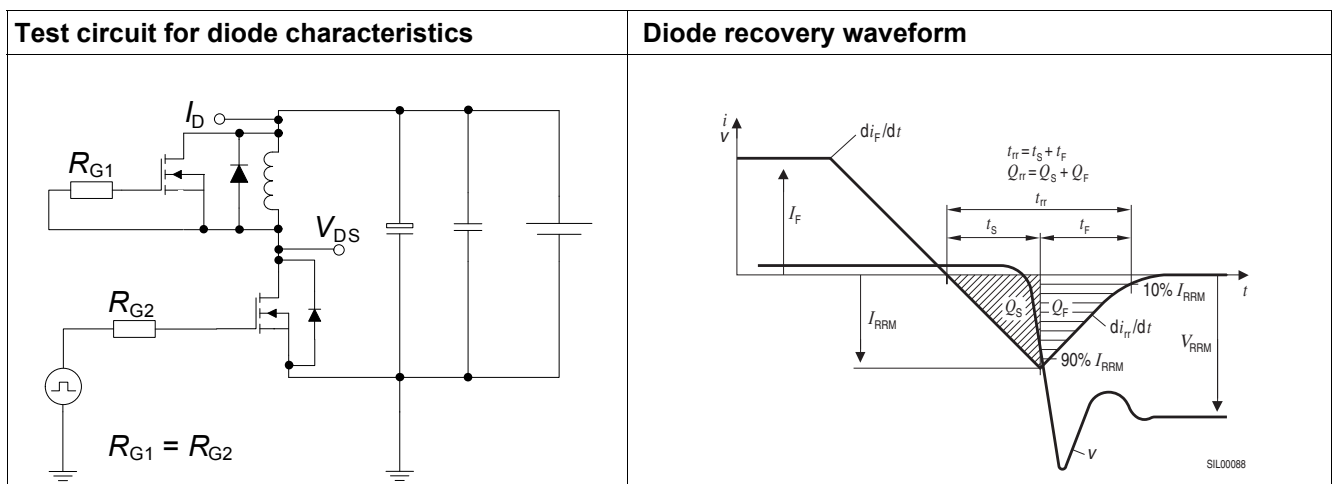
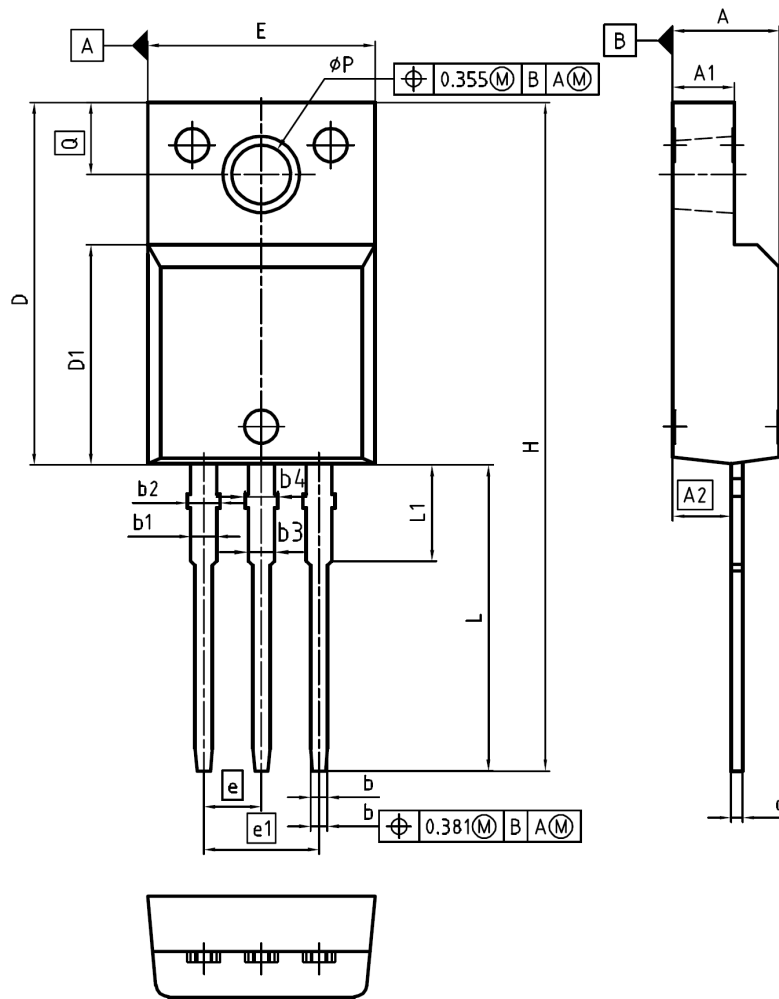


Table 22 Test circuit and waveform for diode characteristics







DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.55	4.85	0.179	0.191
A1	2.55	2.85	0.100	0.112
A2	2.42	2.72	0.095	0.107
b	0.65	0.85	0.026	0.033
b1	0.95	1.33	0.037	0.052
b2	0.95	1.51	0.037	0.059
b3	0.65	1.33	0.026	0.052
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.85	16.15	0.624	0.636
D1	9.53	9.83	0.375	0.387
E	10.35	10.65	0.407	0.419
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H	29.45	29.75	1.159	1.171
L	13.45	13.75	0.530	0.541
L1	3.15	3.45	0.124	0.136
phi P	2.95	3.20	0.116	0.126
Q	3.15	3.50	0.124	0.138

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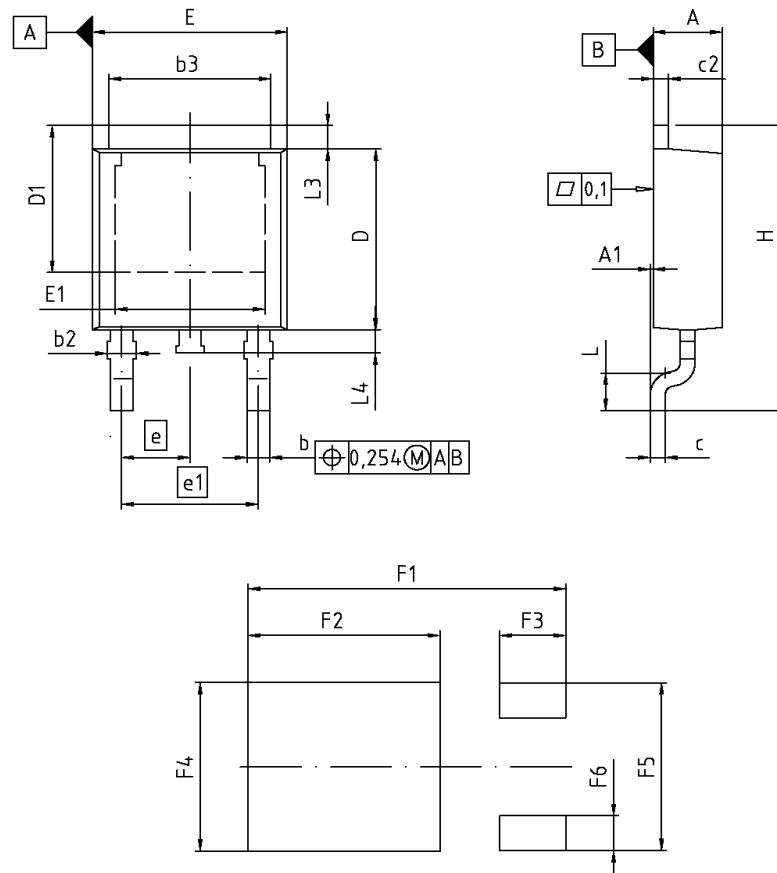
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ISSUE DATE  
08-03-2007

REVISION  
03

Figure 2 Outlines TO-220 FullPAK, dimensions in mm/inches



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b3	5.00	5.50	0.197	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.98	0.018	0.039
D	5.97	6.22	0.235	0.245
D1	5.02	5.84	0.198	0.230
E	6.40	6.73	0.252	0.265
E1	4.70	5.21	0.185	0.205
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L3	0.90	1.25	0.035	0.049
L4	0.51	1.00	0.020	0.039
F1	10.50	10.70	0.413	0.421
F2	6.30	6.50	0.248	0.256
F3	2.10	2.30	0.083	0.091
F4	5.70	5.90	0.224	0.232
F5	5.66	5.86	0.223	0.231
F6	1.10	1.30	0.043	0.051

**DOCUMENT NO.**  
Z8B00003328

**SCALE**

**EUROPEAN PROJECTION**

**ISSUE DATE**  
19-10-2007

**REVISION**  
03

Figure 3 Outlines TO-252, dimensions in mm/inches



## 8 Revision History

### CoolMOS C6 600V CoolMOS™ C6 Power Transistor

Revision History: 2009-09-17, Rev. 2.0

#### Previous Revision:

Revision	Subjects (major changes since last revision)
2.0	Release of final data sheet

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Edition 2009-09-17

Published by  
Infineon Technologies AG  
81726 Munich, Germany

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